

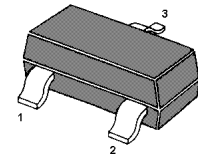
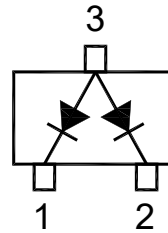
MMBD3004CA-AH

Silicon Epitaxial Planar Switching Diode

High Voltage Switching Diode

Features

- AEC-Q101 Qualified
- Fast switching speed
- High Conductance
- High Reverse Breakdown Voltage Rating
- Halogen and Antimony Free(HAF), RoHS compliant



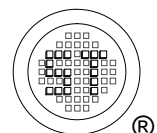
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

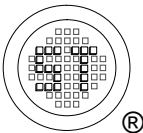
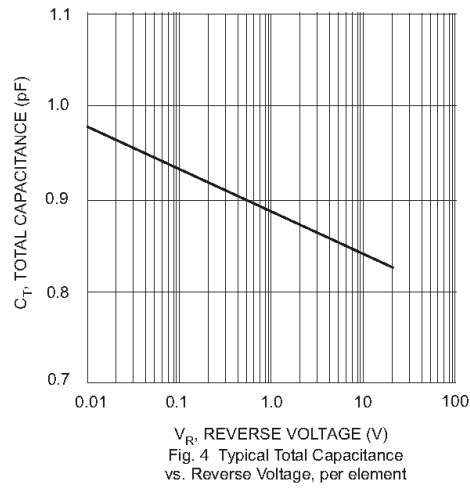
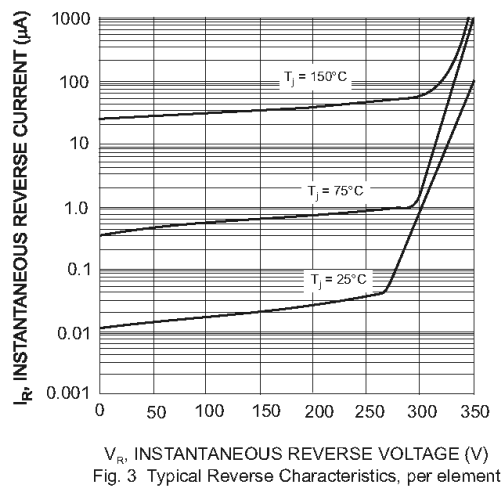
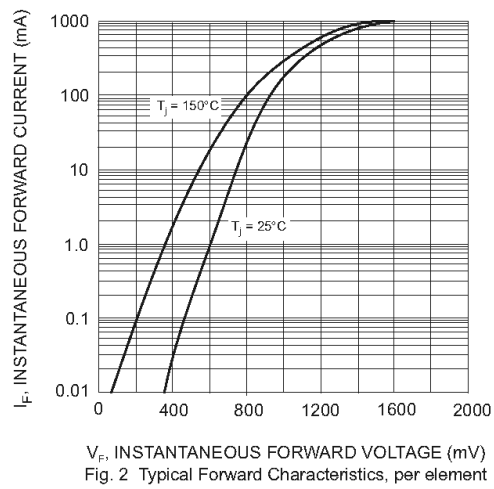
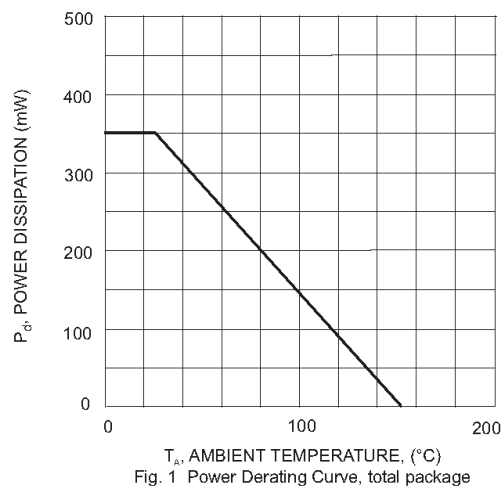
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	350	V
Working Peak Reverse Voltage	V_{RWM}	300	V
DC Blocking Voltage	V_R	300	V
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	1 4	A
		at $t = 1$ s at $t = 1$ μ s	
Power Dissipation	P_d	350	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100$ μ A	$V_{(BR)R}$	350	-	V
Forward Voltage at $I_F = 20$ mA at $I_F = 100$ mA at $I_F = 200$ mA	V_F	- - -	0.87 1 1.25	V
Reverse Current at $V_R = 240$ V at $V_R = 240$ V, $T_j = 150^\circ\text{C}$	I_R	- -	100 100	nA μ A
Total Capacitance at $V_R = 0$, $f = 1$ MHz	C_T	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30$ mA, $I_{rr} = 0.1 I_R$, $R_L = 100$ Ω	t_{rr}	-	50	ns



Electrical Characteristics Curves

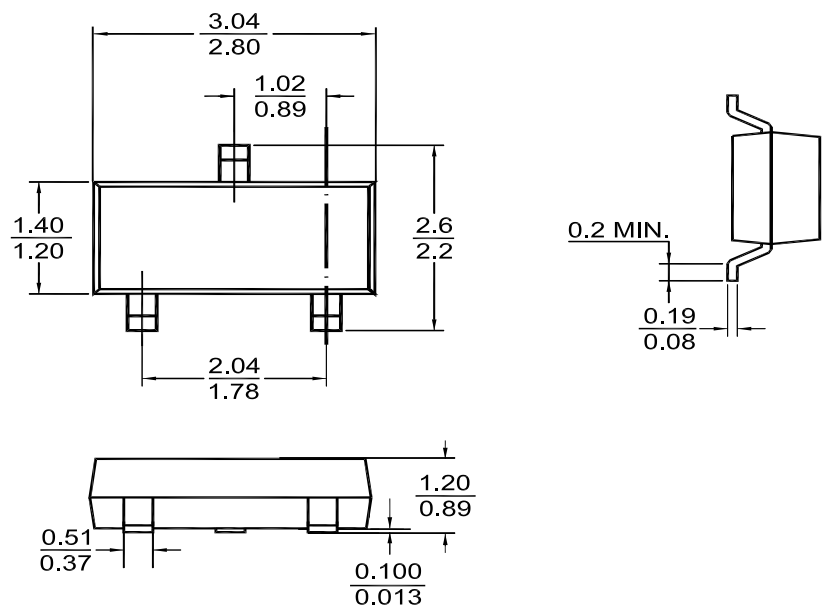


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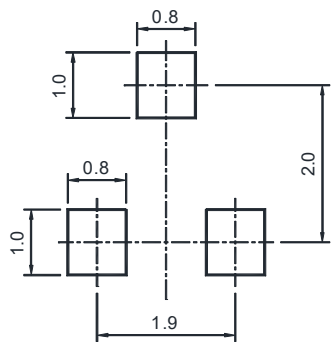
PACKAGE OUTLINE

Plastic surface mounted package (Dimensions in mm)

TO-236



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-236	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

" RA " = Part No.
" • " = HAF (Halogen and Antimony Free)
"YM" = Date Code Marking
"Y" = Year
"M" = Month
Font type: Arial

